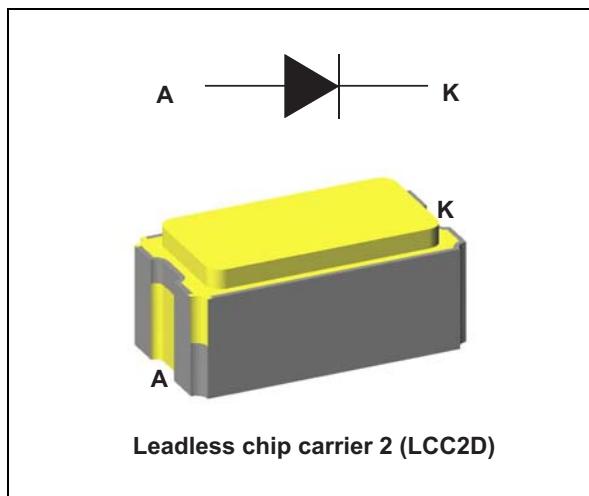


Aerospace 0.3 A - 75 V switching diode

Datasheet - production data



Description

Packaged in LCC2D this device intended for use in low voltage, high frequency inverters, free wheeling, polarity protection and other aerospace applications.

Features

- Surface mount hermetic package
- High thermal conductivity materials
- Very small conduction losses
- Negligible switching losses
- Extremely fast switching
- Low forward voltage drop
- Target radiation qualification
 - 150 krad (Si) low dose rate
 - 3 Mrad (Si) high dose rate
- Package mass: 0.12 g

Table 1. Device summary⁽¹⁾

Order code	ESCC detailed specification	Quality level	Lead finish	EPPL	$I_{F(AV)}$	V_{RRM}	$T_{j(max)}$	$V_{F(max)}$
1N6640UD1		Engineering model	Gold	Yes	0.3	75	175	1,06
1N6640U01D	5101/027/07	ESCC	Gold					
1N6640U02D	5101/027/08	ESCC	Solder dip					

1. Contact ST sales office for information about the specific conditions for products in die form.

1 Characteristics

Table 2. Absolute ratings (limiting values)

Symbol	Parameter	Value	Unit	
V_{RRM}	Repetitive peak reverse voltage	75	V	
$I_{F(RMS)}$	Forward rms current	0.5	A	
$I_{F(AV)}$	Average forward rectified current ⁽¹⁾	300	mA	
I_{FSM}	Forward surge current	$t_p = 8.3 \text{ ms sinusoidal}, t_{amb} \leq 25^\circ\text{C}$	2	A
T_{stg}	Storage temperature range	-65 to +175	$^\circ\text{C}$	
T_j	Operating junction temperature range	-65 to +175	$^\circ\text{C}$	
T_{sol}	Maximum soldering temperature ⁽²⁾	245	$^\circ\text{C}$	

1. For all variants at $T_c \geq +155^\circ\text{C}$ per diode, derate linearly to 0 A at $+175^\circ\text{C}$.
2. Maximum duration 5 s. The same package must not be re-soldered until 3 minutes have elapsed.

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case ⁽¹⁾	60	$^\circ\text{C/W}$
$R_{th(j-a)}$	Junction to ambient	280	

1. Package mounted on infinite heatsink

Table 4. Static electrical characteristics

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
V_{BR} ⁽¹⁾	Breakdown voltage	$T_j = 25^\circ\text{C}$	$I_R = 10 \mu\text{A}$	75	-	-	V
I_R ⁽¹⁾	Reverse current	$T_j = 25^\circ\text{C}$	$V_R = 50 \text{ V}$	-	-	40	nA
		$T_j = 150^\circ\text{C}$		-	-	30	μA
V_F ⁽²⁾	Forward voltage	$T_j = 25^\circ\text{C}$	$I_F = 1 \text{ mA}$	540	-	630	mV
		$T_j = 25^\circ\text{C}$	$I_F = 50 \text{ mA}$	760	-	890	
		$T_j = 25^\circ\text{C}$	$I_F = 100 \text{ mA}$	820	-	980	
		$T_j = 25^\circ\text{C}$	$I_F = 200 \text{ mA}$	870	-	1100	
		$T_j = -55^\circ\text{C}$	$I_F = 200 \text{ mA}$	-	-	1200	

1. Pulse test: $t_p = 10 \text{ ms}$, $\delta < 2\%$
2. Pulse test: $t_p = 680 \mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 0.74 \times I_{F(AV)} + 1.00 \times I_{F(RMS)}^2$$

Table 5. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	$I_F = I_R = 10 \text{ mA}$	-	-	9	ns
		$I_F = 1 \text{ A}, V_r = 30 \text{ V}, dI/dt = -15 \text{ A}/\mu\text{s}$			20	
V_{FP}	Forward recovery voltage	$I_{FM} = 200 \text{ mA}$	-	-	5	V
t_{FR}	Forward recovery time	$I_{FM} = 200 \text{ mA}$	-	-	20	ns
C_j	Diode capacitance	$V_R = 0 \text{ V}, V = 50 \text{ mV}, F = 1 \text{ MHz}$	-	-	3	pF

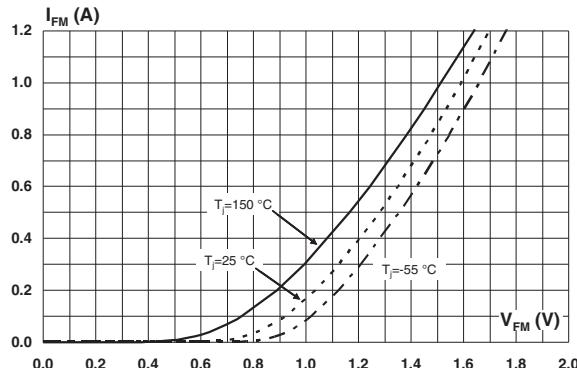
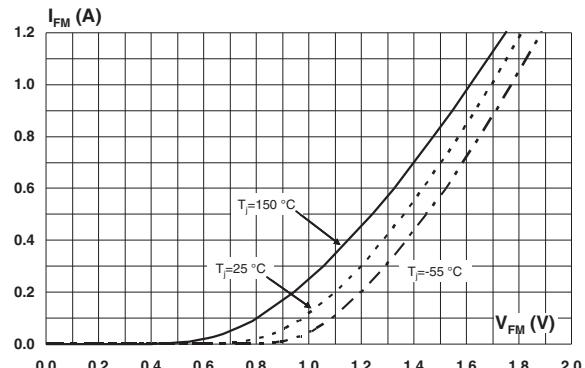
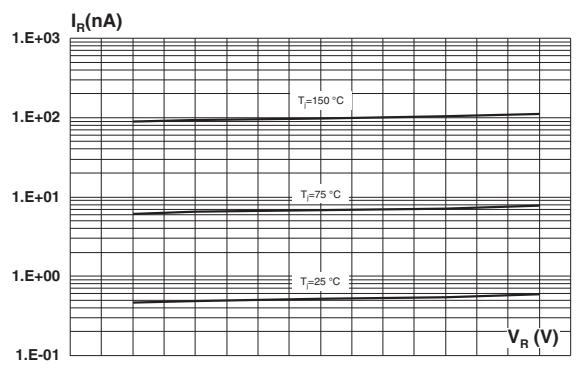
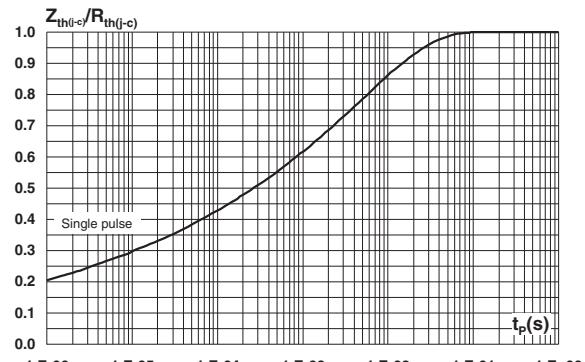
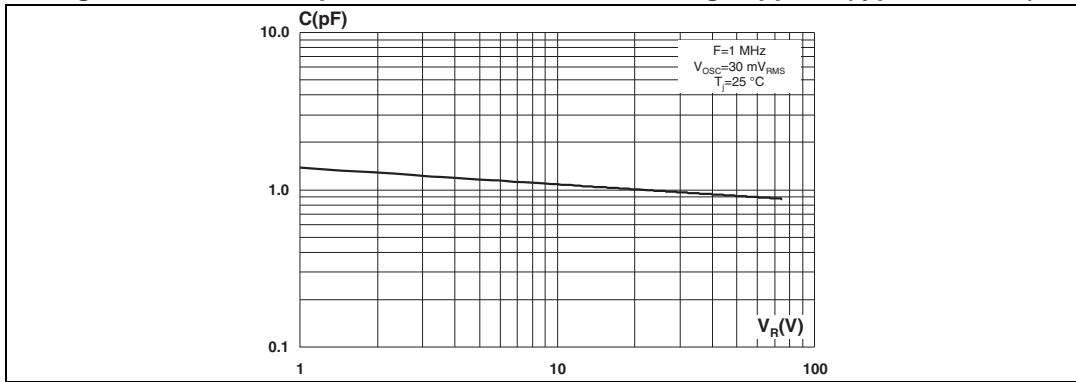
Figure 1. Forward voltage drop versus forward current (typical values)**Figure 2. Forward voltage drop versus forward current (maximum values)****Figure 3. Reverse leakage current versus reverse voltage applied (typical values)****Figure 4. Relative variation of thermal impedance, junction to case, versus pulse duration**

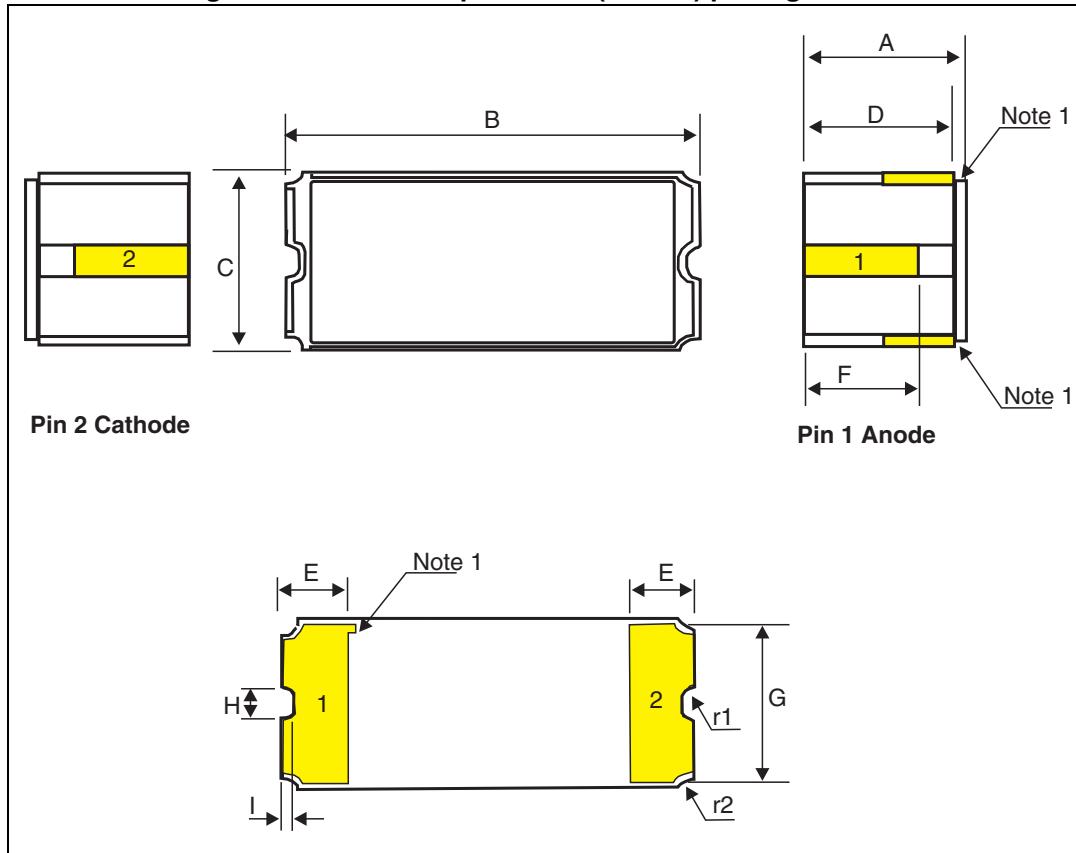
Figure 5. Junction capacitance versus reverse voltage applied (typical values)

2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com.
ECOPACK® is an ST trademark.

2.1 Leadless chip carrier 2 (LCC2D) package information

Figure 6. Leadless chip carrier 2 (LCC2D) package outline



1. The anode is identified by metalization in two top internal angles and the index mark.

Table 6. Leadless chip carrier 2 (LCC2D) package mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A ⁽¹⁾	1.86	2.03	2.20	0.073	0.080	0.087
B	4.44	4.57	4.77	0.175	0.180	0.188
C	1.84	1.97	2.10	0.072	0.078	0.083
D	1.53	1.70	1.87	0.060	0.067	0.074
E	0.48	-	0.71	0.019	-	0.028
F	-	1.3	-	-	0.051	-
G	-	1.67	-	-	0.066	-
H	-	0.37	-	-	0.015	-
I	-	0.15	-	-	0.006	-
r1	-	0.15	-	-	0.006	-
r2	-	0.20	-	-	0.008	-

1. Measurement prior to solder coating the mounting pads on bottom of package

3 Ordering information

Table 7. Ordering information⁽¹⁾

Order code	ESCC detailed specification	Package	Lead finish	Marking ⁽²⁾	EPPL	Mass	Packing
1N6640UD1	-	LCC2D	Gold	1N6640UD1	-	0.12 g	Waffle pack
1N6640U01D	5101/027/07		Gold	510102707	Y		
1N6640U02D	5101/027/08		Solder dip	510102708	Y		

1. Contact ST sales office for information about the specific conditions for products in die form.

2. Specific marking only. The full marking includes in addition:

For the engineering models: ST logo, date code, country of origin (FR).

For ESCC flight parts: ST logo, date code, country of origin (FR), ESA logo, serial number of the part within the assembly lot.

4 Other information

4.1 Date code

Date code is structured as described below:

- EM xyywwz
- ESCC flight yywwz

Where:

- x (EM only): 3, assembly location Rennes (France)
- yy: last two digits year
- ww: week digits
- z: lot index in the week

4.2 Documentation

In [Table 8](#) is a summary of the documentation provided with each type of products.

Table 8. Documentation provided with each type of products

Quality level	Documentation
Engineering model	
ESCC flight	Certificate of conformance

5 Revision history

Table 9. Document revision history

Date	Revision	Changes
26-Mar-2010	1	First issue.
23-Sep-2011	2	Updated order codes in Table 1 Table 7.
8-Nov-2013	3	Updated Table 1, Table 5 and Table 7 and inserted Other information.
04-Dec-2015	4	Updated Table 7 and reformatted to current standard.

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